



Supplementary Materials

The reflectance characteristics of an inverse moth-eye structure in a silicon substrate depending on SF₆/O₂ plasma etching conditions

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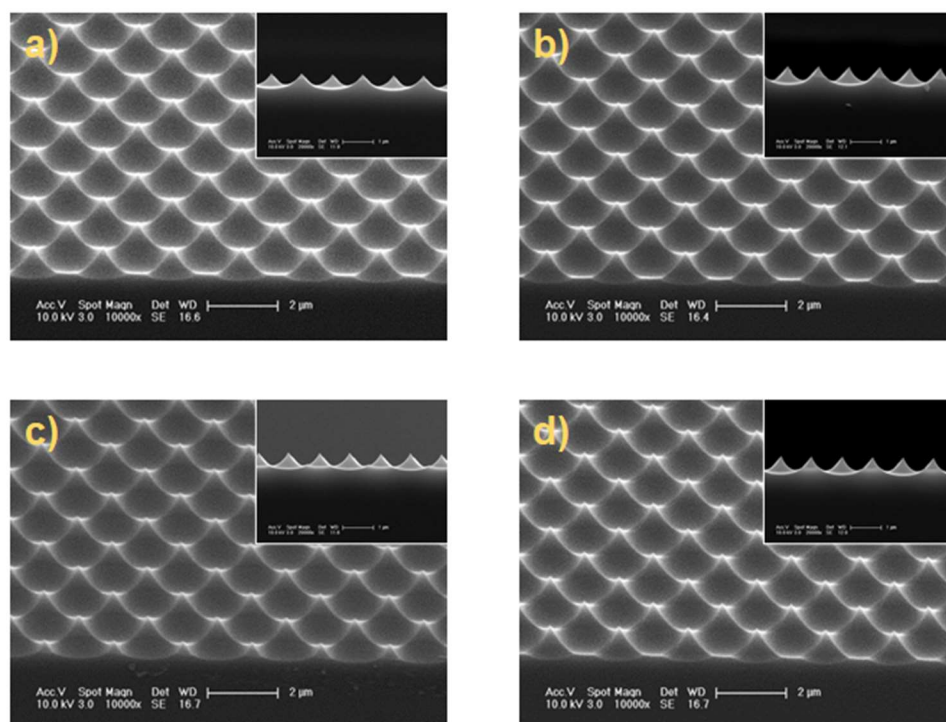


Figure S1. SEM images of an inverse moth-eye microstructure according to O₂ gas addition; (a) 0 sccm, (b) 10 sccm, (c) 20 sccm and (d) 30 sccm

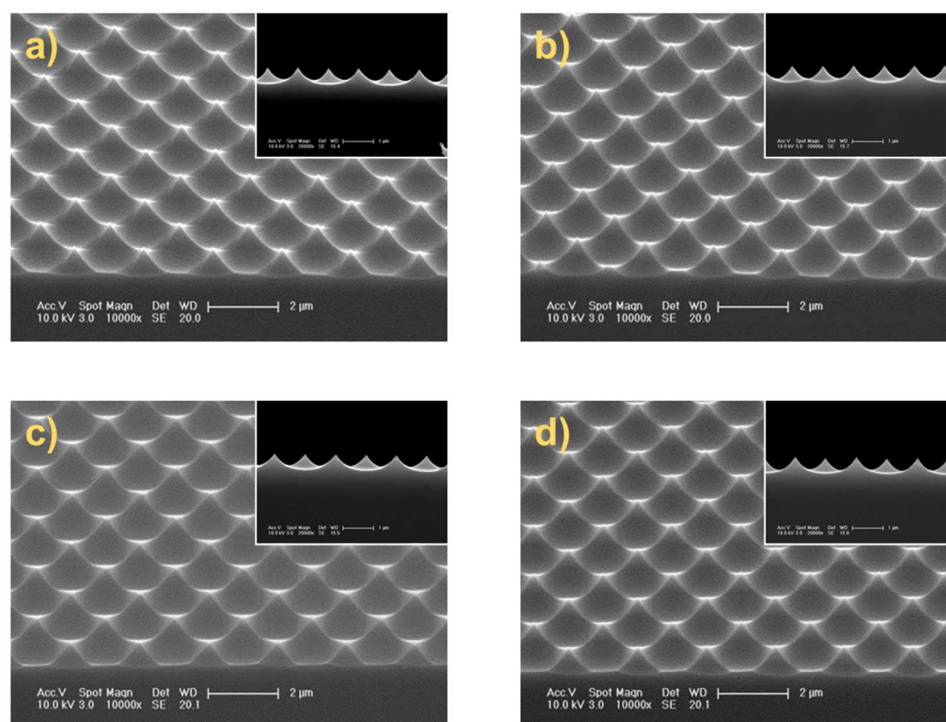


Figure S2. SEM images of an inverse moth-eye microstructure according to upper RF power; (a) 750 W, (b) 800 W, (c) 900 W and (d) 950 W

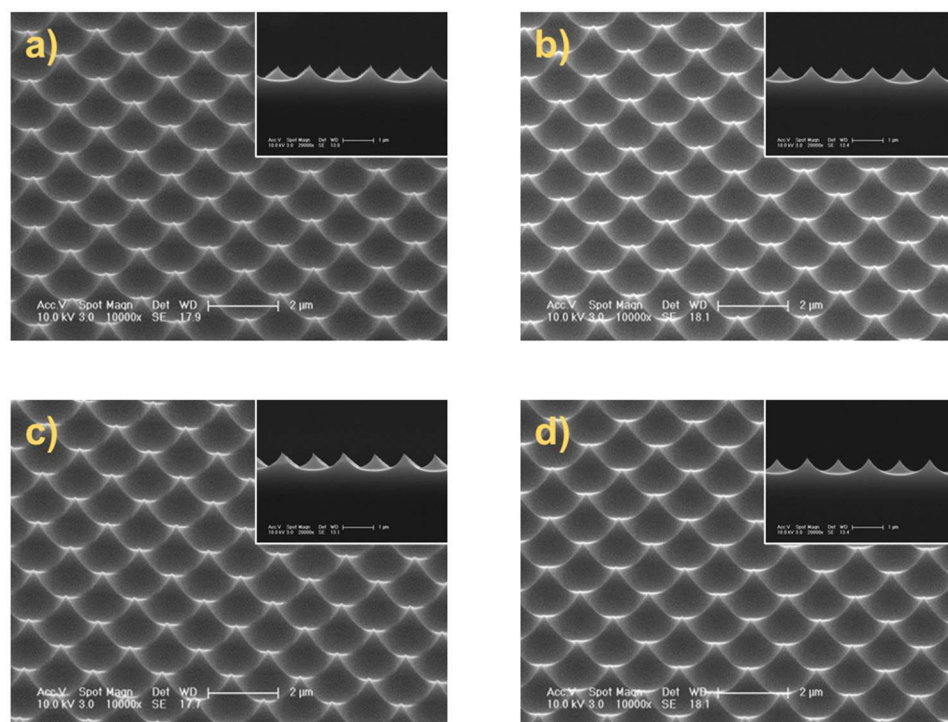


Figure S3. SEM images of an inverse moth-eye microstructure according to process pressure; (a) 25 mTorr, (b) 30 mTorr, (c) 40 mTorr and (d) 45 mTorr